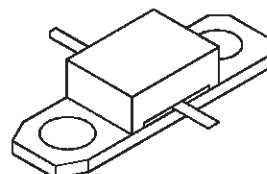


## RF & MICROWAVE TRANSISTORS SATELLITE COMMUNICATIONS APPLICATIONS

- REFRACTORY/GOLD METALLIZATION
- EFFICIENCY - 50% TYPICAL
- $P_{OUT} = 30 \text{ W MIN. WITH } 9.3 \text{ dB GAIN}$



**.250 x .320 2LFL (M170)**  
epoxy sealed

**ORDER CODE**  
SD1899

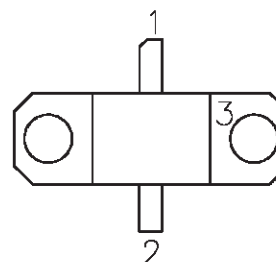
**BRANDING**  
SD1899

### DESCRIPTION

The SD1899 is a common base silicon NPN bipolar device optimized for 1.6 GHz SATCOM applications.

SD1899 offers superior gain and collector efficiency, making it an ideal choice for Class C power amplifiers used in portable as well as fixed SATCOM terminals.

### PIN CONNECTION



1. Collector                      3. Base  
2. Emitter

### ABSOLUTE MAXIMUM RATINGS ( $T_{case} = 25^{\circ}\text{C}$ )

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	45	V
$V_{CES}$	Collector-Emitter Voltage	45	V
$V_{EBO}$	Emitter-Base Voltage	3.0	V
$I_C$	Device Current	3.5	A
$P_{DISS}$	Power Dissipation (+25°C)	64.8	W
$T_J$	Junction Temperature	+200	°C
$T_{STG}$	Storage Temperature	- 65 to +150	°C

### THERMAL DATA

$R_{TH(j-c)}$	Junction-Case Thermal Resistance	2.7	°C/W
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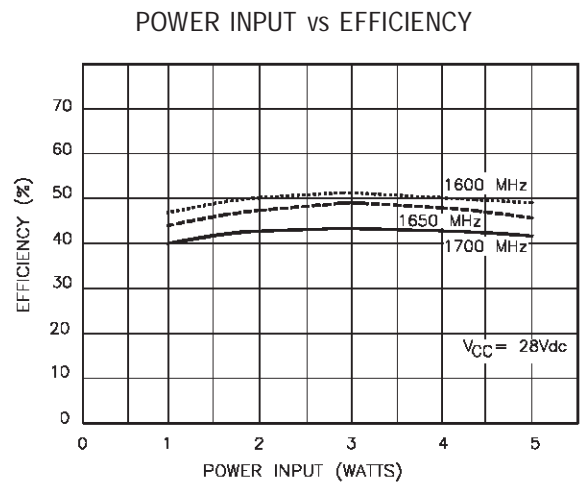
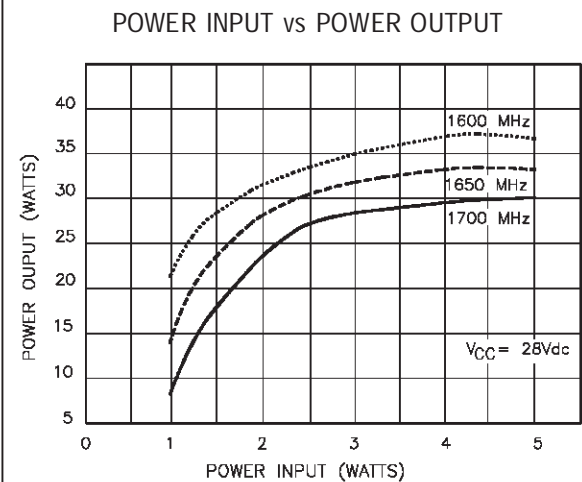
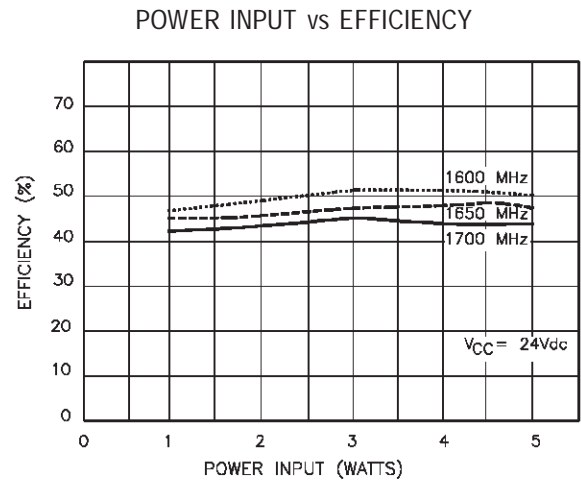
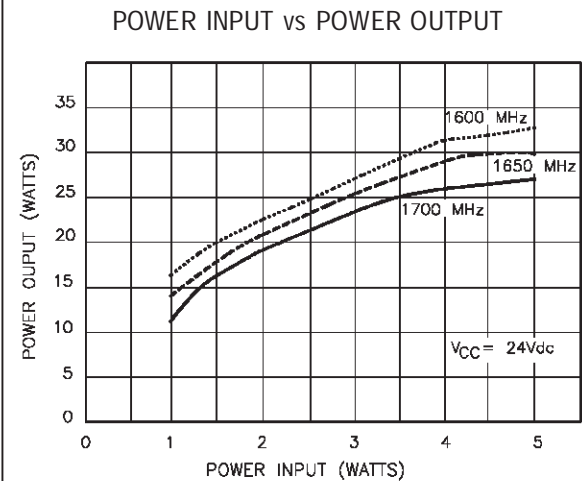
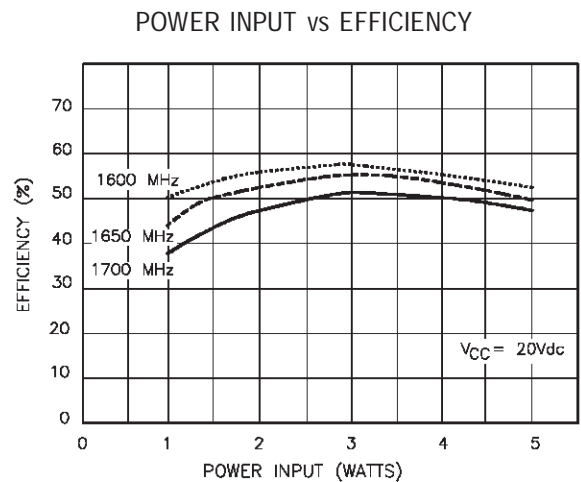
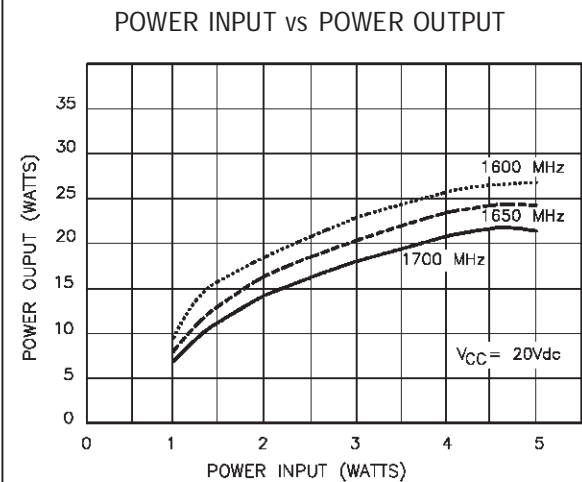
**ELECTRICAL SPECIFICATIONS** ( $T_{\text{case}} = 25^{\circ}\text{C}$ )**STATIC**

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
$BV_{\text{CBO}}$	$I_{\text{C}} = 8 \text{ mA}$	$I_{\text{E}} = 0 \text{ mA}$	45	—	—	V
$BV_{\text{CES}}$	$I_{\text{C}} = 8 \text{ mA}$	$V_{\text{BE}} = 0 \text{ V}$	45	—	—	V
$BV_{\text{EBO}}$	$I_{\text{E}} = 8 \text{ mA}$	$I_{\text{C}} = 0 \text{ mA}$	3.0	—	—	V
$I_{\text{CBO}}$	$V_{\text{CB}} = 28 \text{ V}$	$I_{\text{E}} = 0 \text{ mA}$	—	—	2	mA
$h_{\text{FE}}$	$V_{\text{CE}} = 5 \text{ V}$	$I_{\text{C}} = 1.6 \text{ A}$	15	—	150	—

**DYNAMIC**

Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
$P_{\text{OUT}}$	$f = 1650 \text{ MHz}$	$V_{\text{CC}} = 28 \text{ V}$	$P_{\text{IN}} = 3.5 \text{ W}$	30	32	—	W
$\eta_{\text{c}}$	$f = 1650 \text{ MHz}$	$V_{\text{CC}} = 28 \text{ V}$	$P_{\text{IN}} = 3.5 \text{ W}$	45	50	—	%
$P_{\text{G}}$	$f = 1650 \text{ MHz}$	$V_{\text{CC}} = 28 \text{ V}$		9.3	—	—	dB

TYPICAL PERFORMANCE



## TEST CIRCUIT

